

RF Oxygen Discharge Cleaning of Carbon from EUV Optics

Sponsored by

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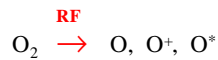
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INTRODUCTION

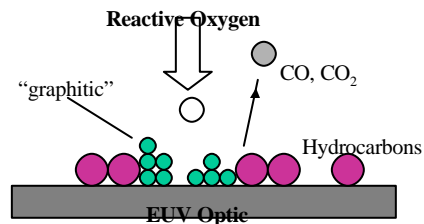
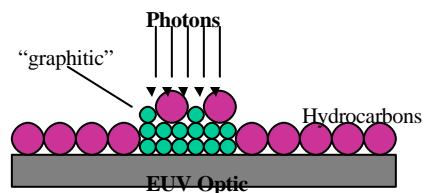
- Carbon deposition (due to hydrocarbon cracking) an issue for EUVL
- Develop in-situ cleaning methodology:
 - Remote O₂ / RF discharge



Issues:

- Carbon Removal Rates
- Efficiently clean over large distances

Buried/obstructed optics



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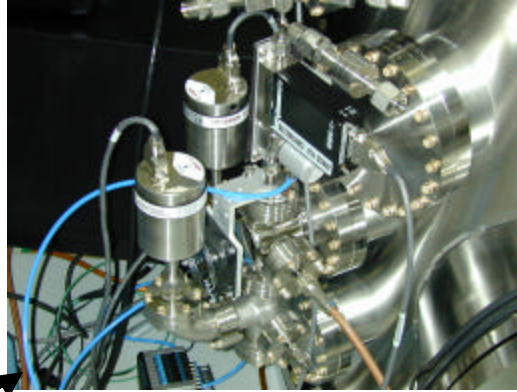
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RF Oxygen Cleaning Using Model Geometry

Multi-use Vacuum Chamber:
8ft tall, 33 inches wide

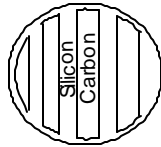
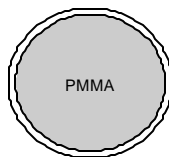


RF Appendage Cell

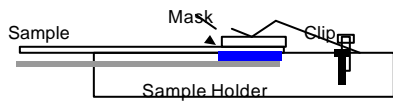
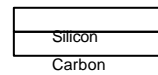
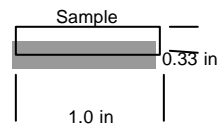


Samples for Model Geometry

- Samples: 6 inch Si wafers coated with Carbon or PMMA.

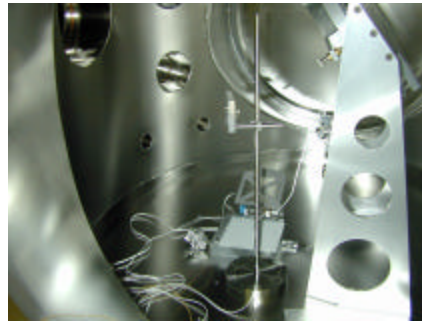
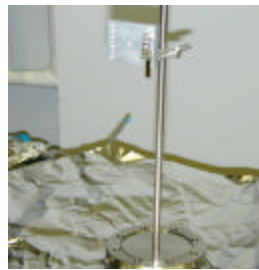
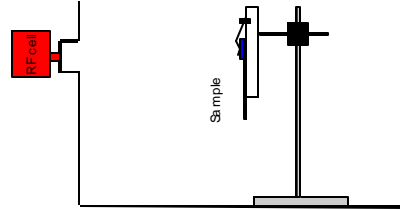


6 inch wafer
with PMMA
or sputtered
Carbon



- Control Region created by masking part of the sample.....No Cleaning

Mounting Configuration



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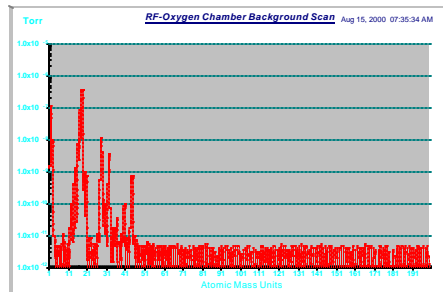
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Tests and Analysis Methods

- Research Purity O₂: 99.998%
- Background Environmental Conditions exceptionally clean chamber.



- Carbon cleaning efficiency determined by Auger Electron Microscopy.
- Resist Removal rates determined by white light spectroscopy (Nanospec AFT 4000)
- Background Environmental Conditions determined using RGA.

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Laboratory

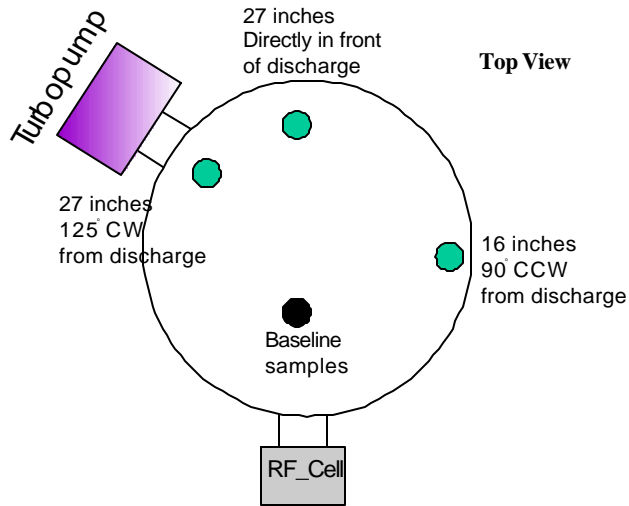
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EUVL

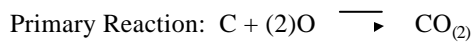
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Sample Locations



Resist Removal Rates : Baseline Study

Oxygen/ RF Discharge 10 inches from source



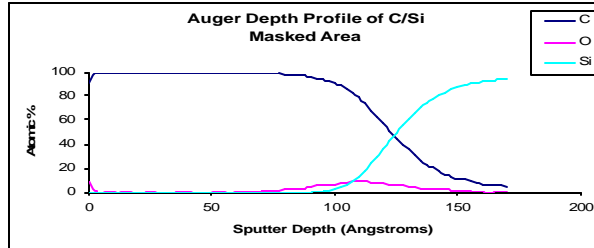
	50sccm (11 mTorr)	100 sccm (19 mTorr)	150sccm (27 mTorr)
50W	58 Å/hr	85 Å/hr	81 Å/hr
100W	65 Å/hr	90 Å/hr	96 Å/hr
200W	92 Å/hr	106 Å/hr	113 Å/hr

Accuracy: +/- 1%

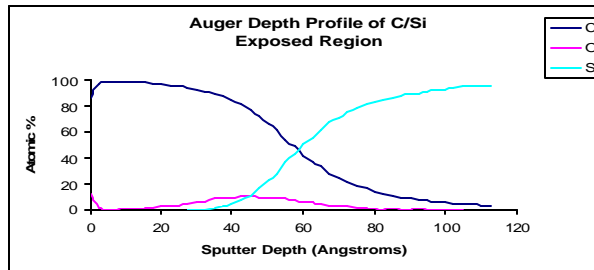
Carbon Removal Analysis

1Hr @ 50W/ 100 sccm 10 inches from port

Masked



Exposed

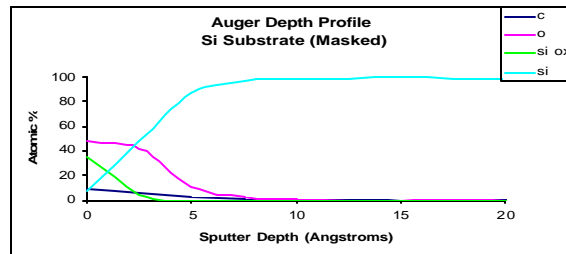


» 70 Å/Hr removed

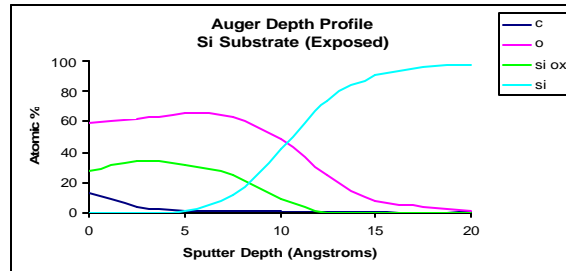
Silicon Oxidation Analysis

4 Hrs @ 50W/ 100 sccm 10 inches from port

Masked



Exposed



» 2.5 Å/Hr oxidation rate

Carbon Cleaning vs Sample Position

150 sccm O₂, 100 W RF Power

Position	Orientation	Removal Rate (Ang./ Hr.)
16" away, 90° CCW	Facing	50
16" away, 90° CCW	Not Facing	31
27" away, 125° CW	Facing	40
27" away, 125° CW	Not Facing	30
27" away, 0°	Facing	20
27" away, 0°	Not Facing	5

Conclusions

- Oxygen RF Discharge cleaning can remove carbon from optic surfaces.
 - High Removal Rates: sufficient for ETS
 - Cleaning is effective at least up to 27 inches downstream.
 - LOS/NLOS variations observed.
 - Si oxidation an issue
- Future tests on "Buried" Optic Geometries are planned.